

YJ Planar Schottky Barrier Diode Die Specification

40V 3A, 55mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB055N040SS-280A

Main Products Characterstics

- Average forward current: $I_F(AV) = 3\text{ A}$
- Maximum operating junction temperature: $T_j = 125\text{ }^{\circ}\text{C}$
- ESD rating: >8KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

Rating	Symbol
	V_{BR}
$I_F = 3\text{ A}$ Pulse Test: $t_p = 300\text{ }\mu\text{s}$, $\delta \leq 2\%$	
Maximum reverse current $V_R = V_{RRM}$ Pulse Test: $t_p = 300\text{ }\mu\text{s}$, $\delta \leq$	I_R

Device Schematics and Outline Drawing

- Die Thickness *
- Die Size **
- Top Metal Pad
- Active Area
- Top Metal
- Back Metal Ag
- Note: 1 * : Also can offer device with 8 mils thickness
- 2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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